SSC80213GN6

P-Channel Enhancement Mode MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D
-20V	±12V	2.2mΩ@-4V5	-120A
		3mΩ@-2V5	

➢ Description

This SSC80213GN6 uses advanced trench technology to provide excellent RDSON and low gate charge. The complementary MOSFETS may be used to form a level shifted high side switch, and for a host of other applications.

100% UIS + ΔVDS + Rg Tested!

➢ Applications

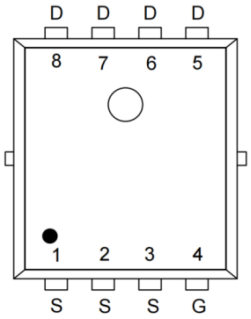
- Load Switch
- PWM Application
- Power Management

➢ Ordering Information

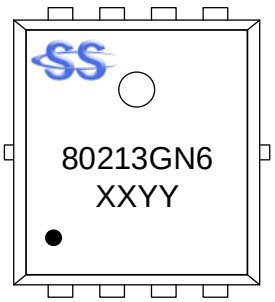
Device	Package	Shipping
SSC80213GN6	PDFN5X6-8L	5000/Reel

➢ Pin configuration

PDFN5X6-8L(Top View)



Pin Configuration



Marking

(XXYY: Internal Traceability Code)

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DSS}	Drain-to-Source Voltage		-20	V
V_{GSS}	Gate-to-Source Voltage		±12	V
I_D	Continuous Drain Current [d]	T_C=25℃	-120	A
		T_C=100℃	-64	
I_{DSM}	Continuous Drain Current [a]	T_A=25℃	-37	A
		T_A=70℃	-27	
I_{DM}	Pulsed Drain Current [b]		-480	A
P_D	Power Dissipation [c]	T_C=25℃	50	W
		T_C=100℃	20	
P_{DSM}	Power Dissipation [a]	T_A=25℃	4.8	W
		T_A=70℃	3	
E_{AS}	Avalanche Energy [b] L=0.5mH Single Pulse		210	mJ
T_J	Operation junction temperature		-55~150	℃
T_{STG}	Storage temperature range		-55~150	

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	26	33	℃/W
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	2.5	3.1	

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper, in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.

b. Repetitive rating, pulse width limited by junction temperature.

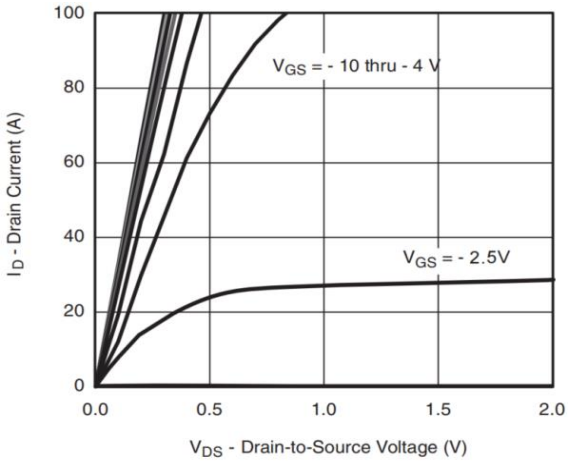
c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

d. The maximum current rating is package limited.

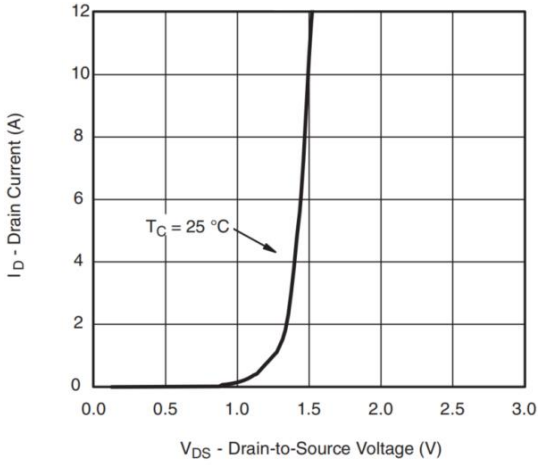
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250uA	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250uA	-0.4	-0.7	-1	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -4.5V, I_D = -20A		2.2	2.8	mΩ
		V_{GS} = -2.5V, I_D = -10A		3	3.9	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -20V, V_{GS} = 0V			-1	μA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±12V, V_{DS} = 0V			±100	nA
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = -10A		-0.8	-1.2	V
Gate Resistance	R_G	V_{DS} = 0V, f = 1MHz		5.7		Ω
Input Capacitance	C_{ISS}	V_{DS} = -10V, V_{GS} = 0V, f = 1MHz		8380		pF
Output Capacitance	C_{OSS}			1375		
Reverse Transfer Capacitance	C_{RSS}			725		
Total Gate Charge	Q_G	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -20A		90		nC
Gate to Source Charge	Q_{GS}			18		
Gate to Drain Charge	Q_{GD}			31		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = -4.5V, V_{DS} = -10V, R_L = 2Ω, R_G = 3Ω		18		ns
Rise Time	T_r			48		
Turn-off Delay Time	$T_{D(OFF)}$			100		
Fall Time	T_f			40		

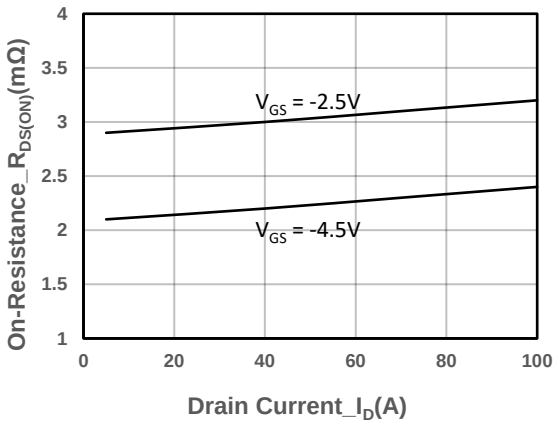
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



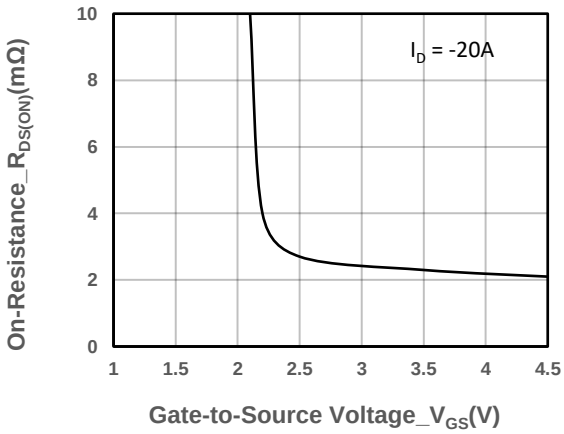
Output Characteristics



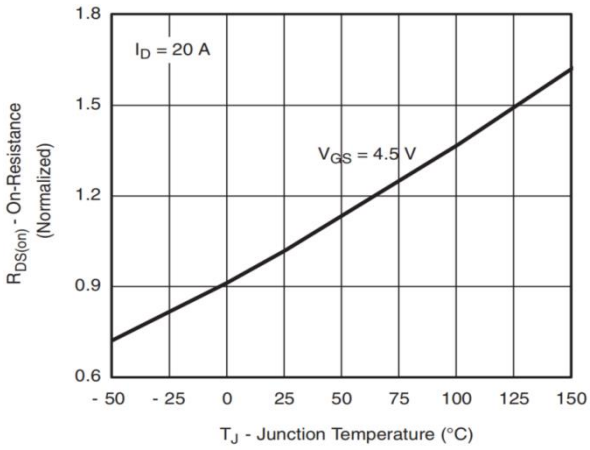
Transfer Characteristics



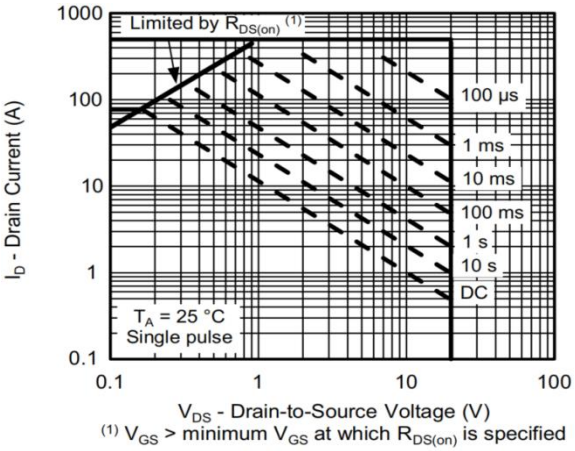
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage

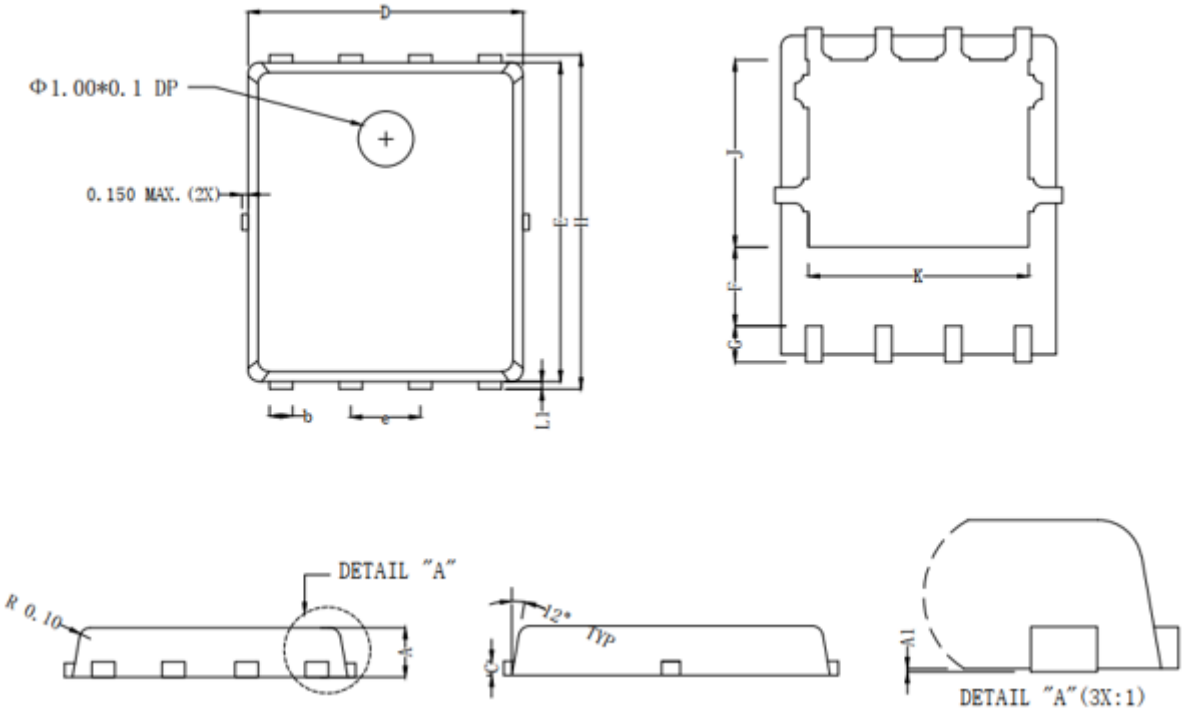


On-Resistance vs. Junction Temperature



Safe Operating Area, Junction-to-Ambient

➢ Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.90	1.00	1.10
A1	0.00	0.03	0.05
b	0.25	0.03	0.35
c		0.254 REF	
D	4.80	4.90	5.00
F		1.35 REF	
E	5.65	5.75	5.85
e		1.27 BSC	
H	5.90	6.00	6.10
L1	0.10	0.13	0.16
G		0.55 REF	
K		4.00 REF	
J		3.45 REF	

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